

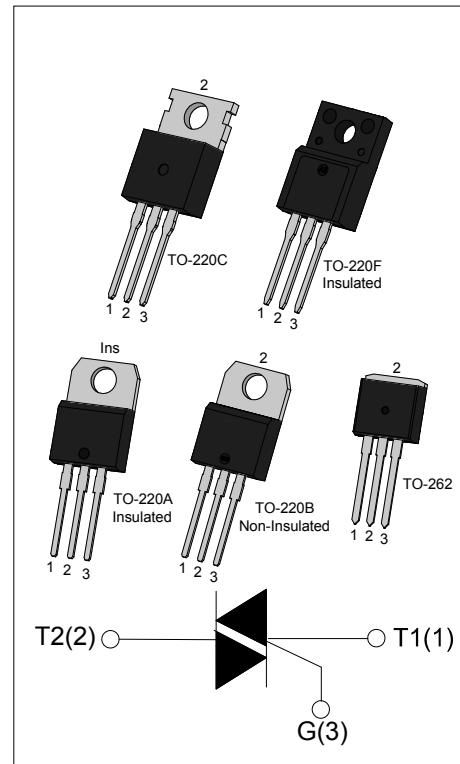


JST12 Series 12A TRIACS

Rev.8.0

DESCRIPTION:

With high ability to withstand the shock loading of large current, JST12 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load. From all three terminals to external heatsink, JST12A provides a rated insulation voltage of 2500 V_{RMS}, and JST12F provides a rated insulation voltage of 2000 V_{RMS}, complying with UL standards (File ref: E252906). All the packages above are RoHS compliant. (2011/65/EU)



MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	12	A
V _{DRM} /V _{RRM}	600/800/1200	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T _{stg}	-40-150	°C
Operating junction temperature range	T _j	-40-125	°C
Repetitive peak off-state voltage (T _j =25°C)	V _{DRM}	600/800/1200	V
Repetitive peak reverse voltage (T _j =25°C)	V _{RRM}	600/800/1200	V
Non repetitive surge peak Off-state voltage	V _{DSM}	V _{DRM} +100	V
Non repetitive peak reverse voltage	V _{RSM}	V _{RRM} +100	V
RMS on-state current	TO-220A(Ins) (T _c =85°C)	I _{T(RMS)}	12
	TO-262/		
	TO-220B(Non-Ins)/		
	TO-220C(T _c =100°C)		
TO-220F(Ins) (T _c =80°C)			

Non repetitive surge peak on-state current (full cycle, F=50Hz)	I _{TSM}	120	A	
I ² t value for fusing (tp=10ms)	I ² t	78	A ² s	
Critical rate of rise of on-state current (I _G =2×I _{GT})	I - II - III	dI/dt	50	A/μs
Peak gate current	I _{GM}	4	A	
Average gate power dissipation	P _{G(AV)}	1	W	
Peak gate power	P _{GM}	5	W	

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

3 Quadrants

Symbol	Test Condition	Quadrant		Value				Unit
				BW	CW	SW	TW	
I _{GT}	V _D =12V R _L =33Ω	I - II - III	MAX	50	35	10	5	mA
V _{GT}		I - II - III	MAX	1.3				V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	I - II - III	MIN	0.2				V
I _L	I _G =1.2I _{GT}	I - III	MAX	80	50	30	20	mA
		II		90	60	40	30	
I _H	I _T =100mA	MAX		60	40	20	15	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125°C	MIN		1000	500	200	100	V/μs
(dI/dt)c	Without snubber T _j =125°C	MIN		12	6.5	-	-	A/ms

4 Quadrants

Symbol	Test Condition	Quadrant		Value		Unit	
				B	C		
I _{GT}	V _D =12V R _L =33Ω	I - II - III	MAX	50	25	mA	
		IV		70	50		
V _{GT}	ALL	MAX		1.3			
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	ALL	MIN	0.2			
I _L	I _G =1.2I _{GT}	I - III - IV	MAX	50	40	mA	
		II		100	80		

I _H	I _T =100mA	MAX	50	25	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125°C	MIN	500	200	V/μs
(dV/dt)c	(dI/dt)c=5.3A/ms T _j =125°C	MIN	10	5	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter	Value(MAX)	Unit
V _{TM}	I _{TM} =17A tp=380μs	1.5	V
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	5
I _{RRM}		T _j =125°C	1

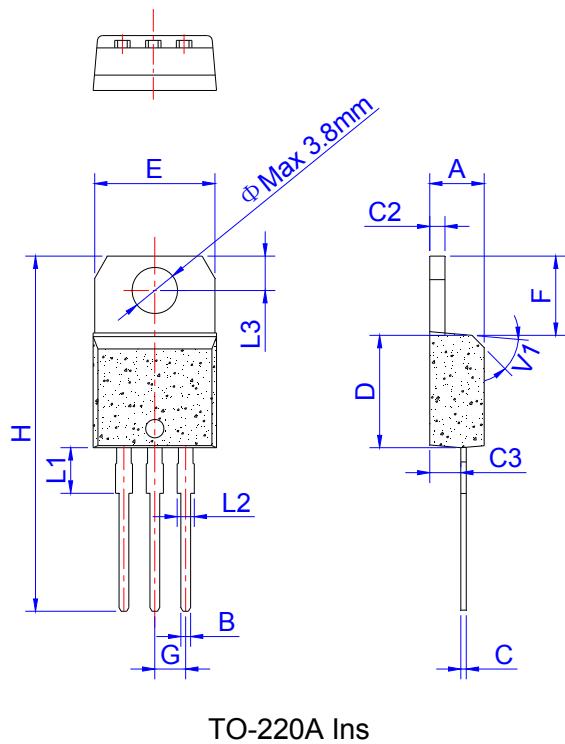
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case(AC)	TO-220A(Ins)	2.3
		TO-262/ TO-220B(Non-Ins)/ TO-220C	1.4
		TO-220F(Ins)	2.5

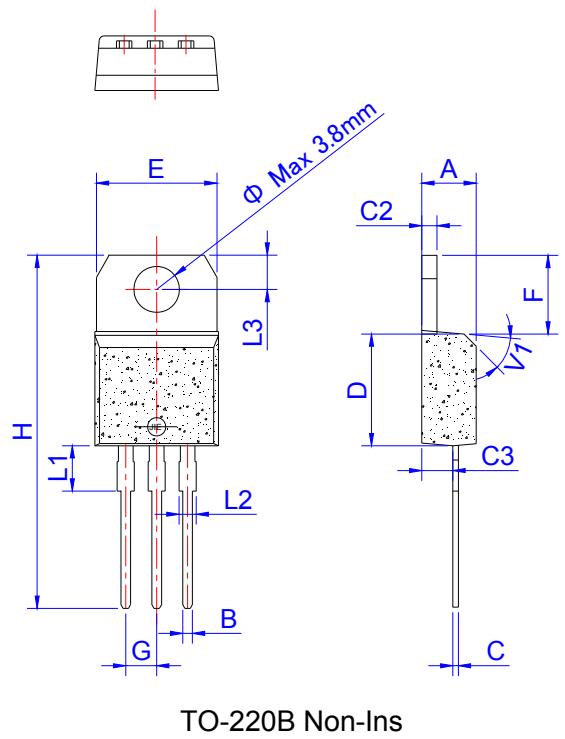
ORDERING INFORMATION

J	ST	12	A	-600	BW
JieJie Microelectronics Co.,Ltd	Triacs	It(RMS):12A			BW:IGT1-3≤50mA CW:IGT1-3≤35mA SW:IGT1-3≤10mA TW:IGT1-3≤5mA B:IGT1-3≤50mA IGT4≤70mA C:IGT1-3≤25mA IGT4≤50mA 600:V _{DRM} /V _{RRM} ≥600V 800:V _{DRM} /V _{RRM} ≥800V 1200:V _{DRM} /V _{RRM} ≥1200V

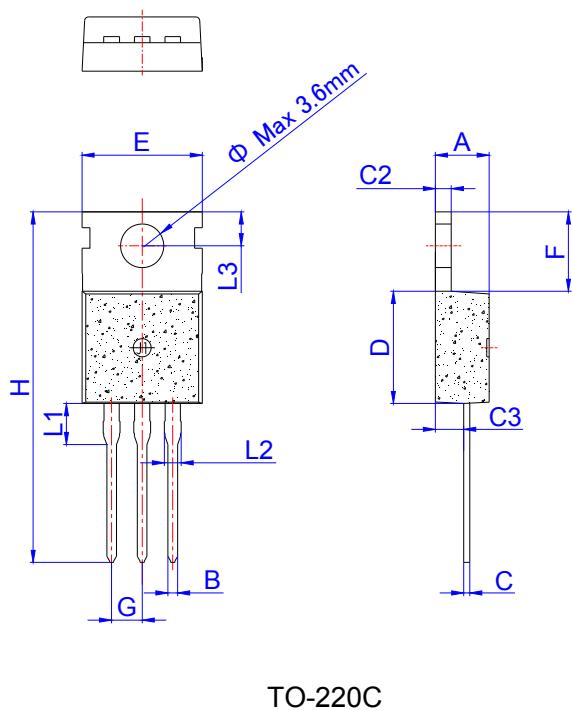
PACKAGE MECHANICAL DATA



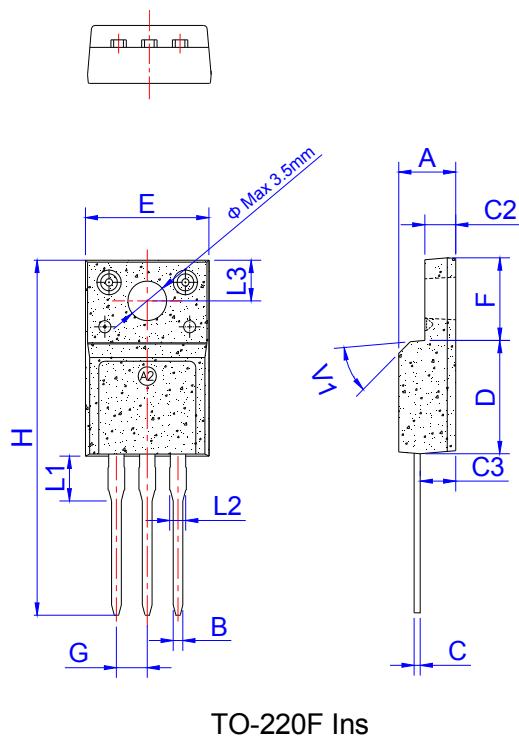
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

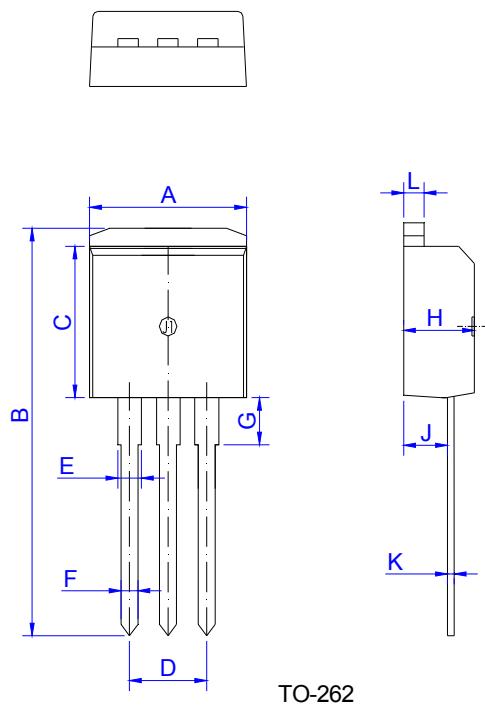
PACKAGE MECHANICAL DATA


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	



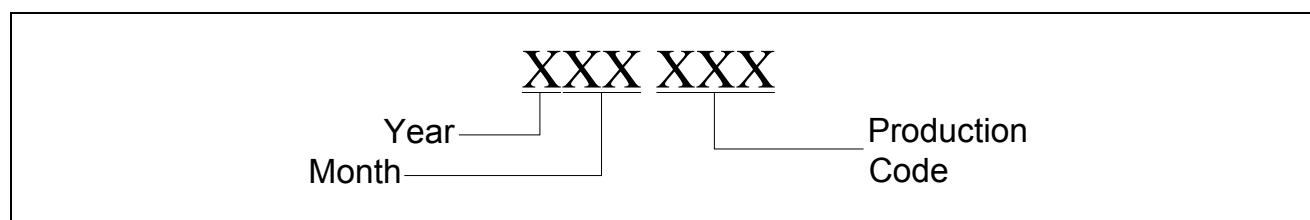
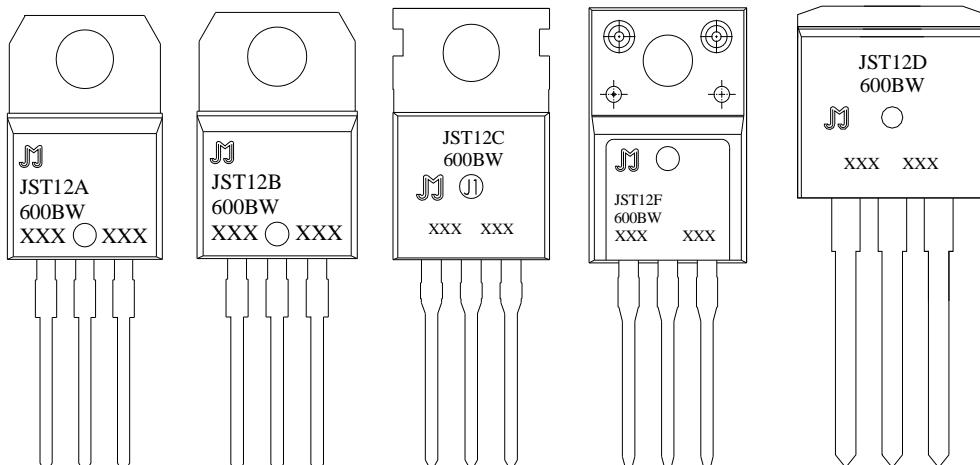
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.95		10.20	0.392		0.402
B	23.25		23.45	0.915		0.923
C	8.90		9.10	0.35		0.358
D	5.00		5.20	0.197		0.205
E	1.20		1.35	0.047		0.053
F	0.80		0.85	0.031		0.033
G	3.30		3.60	0.130		0.142
H	4.45		4.55	0.175		0.179
J	2.50		2.70	0.098		0.106
K	0.38		0.42	0.015		0.017
L	1.25		1.29	0.049		0.051

MARKING



PACKAGE INFORMATION

PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	8,000
TO-220B	TUBE	50	1,000	8,000
TO-220C	TUBE	50	1,000	8,000
TO-220F	TUBE	50	1,000	8,000
TO-262	TUBE	50	1,000	8,000
PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-262	TAPING	800	4,000	13 inch

FIG.1 Maximum power dissipation versus RMS on-state current

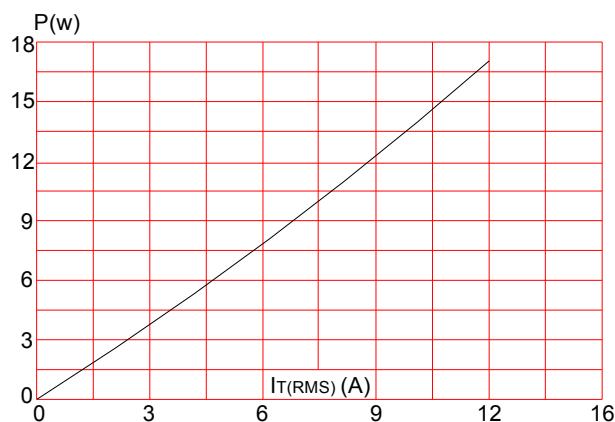


FIG.3: Surge peak on-state current versus number of cycles

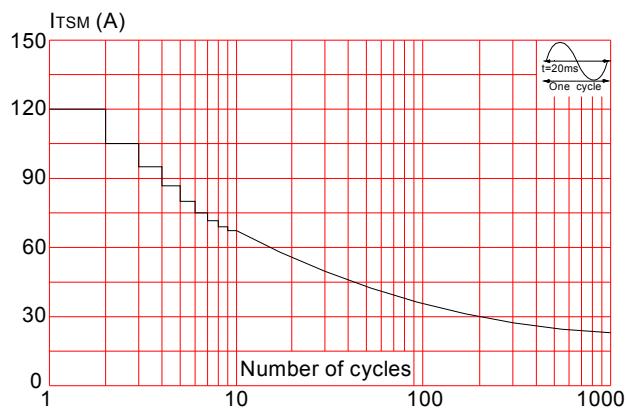


FIG.2: RMS on-state current versus case temperature

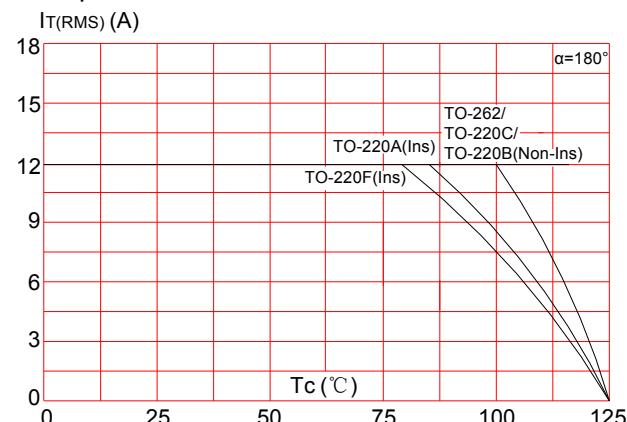


FIG.4: On-state characteristics (maximum values)

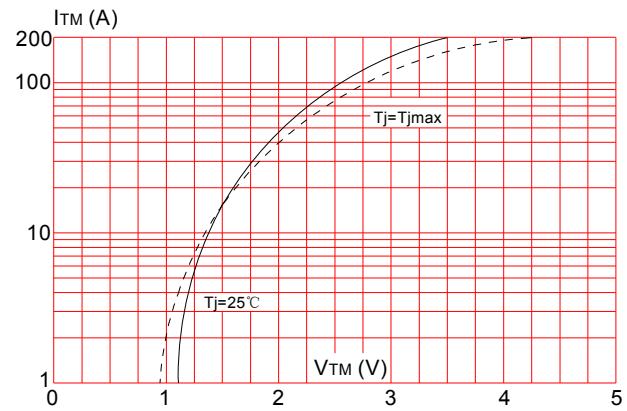


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt|_{I=I_{TSM}} < 50\text{A}/\mu\text{s}$)

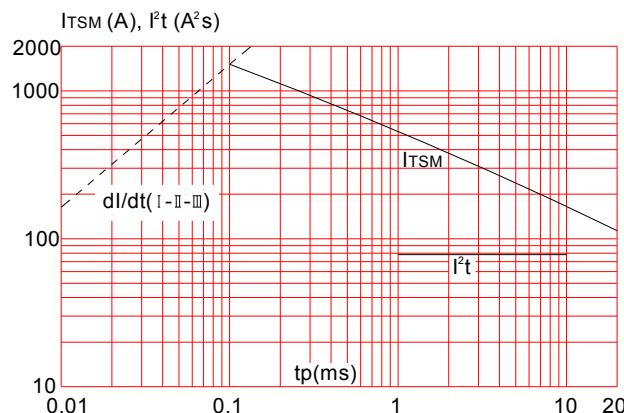
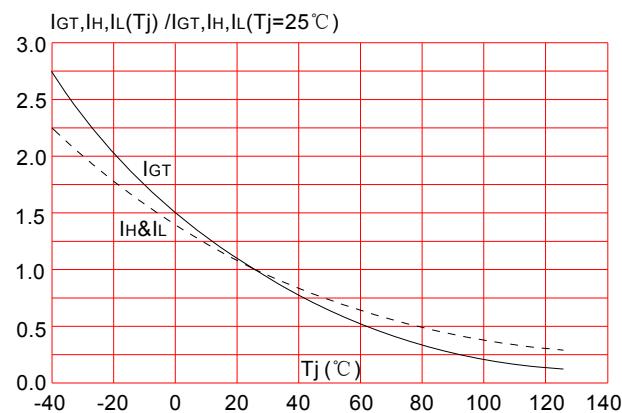


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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